

1989 GaAs REL WORKSHOP PROGRAM
Sunday, October 22, Sheraton Harbor Island Hotel, San Diego, CA.

SESSION I - TECHNIQUES & METHODOLOGY

OPTICAL SCREENING OF GaAs FETs FOR PREMATURE FAILURE, W. Slusark*, D. McGee, R. Menna, T. Bibby, and P. Czajkowski, David Samoff Research Center and *AT&T Bell Laboratories.

THE OBSERVATION OF GATE LAG IN HIGH TEMPERATURE STRESSED GaAs MMIC SWITCHES, Peter Ersland and Jeff Parker, MIA-COM Advanced Semiconductor Division.

CHANNEL TEMPERATURE DEFINITION AND MEASUREMENT, Donald J. LaCombe, General Electric Company.

QML, E.B. Hakim, US Army LABCOM

SESSION 11 - FAILURE MECHANISMS

REVIEW OF GaAs DEVICE FAILURE MECHANISMS, W. T. Anderson, Naval Research Laboratory.

ELECTROMIGRATION IN THIN FILMS OF Au ON SEMI-INSULATING GaAs, P.F. Tang, A.G. Milnes, C.L. Bauer, and S. Mahajan, Camegie Mellon University.

A COMPARATIVE STUDY ON RELIABILITY OF GaAs FETs WITH Al AND Au GATES, T. Ishikawa, M. Katsumata, T. Fujii, Y. Mitsui, and K. Nisitani, Mitsubishi Electric Corporation.

PREDICTION OF PULSED POWER FAILURES THRESHOLD OF GaAs FETS, R. Zuleeg and R.B. Krein, McDonnell Douglas Electronic Systems Company.

SESSION III - PANEL - LUNCHEON DISCUSSION GROUP SUMMARIES, Bill Roesch, TriQuint

TEST STRUCTURES, Martin Buehler, Jet Propulsion Laboratory.

MATERIALS, Gary Troeger, McDonnell Douglas.

ACCELERATED TESTING, Willis Horth, RADAC.

FAILURE MECHANISMS, Ron Clarke, TRW

COST AND METHODOLOGY, Dwane Ragel, Texas Instruments.

SESSION IV - RELIABILITY TEST RESULTS

RELIABILITY STUDY OF GALLIUM ARSENIDE TRANSISTORS, K. Chao, R.H. Maurer, and E. Nhan, John Hopkins University.

AN L-BAND LOW-NOISE MMIC AMPLIFIER USING SAGFETS, K. Nakahara, M. Katsumata, Y. Yoshii, T. Shimura, and O. Ishihara, Mitsubishi Electric Corporation.

RELIABILITY LIFE TESTS, OF GaAs COMPLIMENTARY JFET 1K STATIC RAMS, B. Maderic and G. Troeger, McDonnell Douglas Electronic Systems